PROCESS CP382X

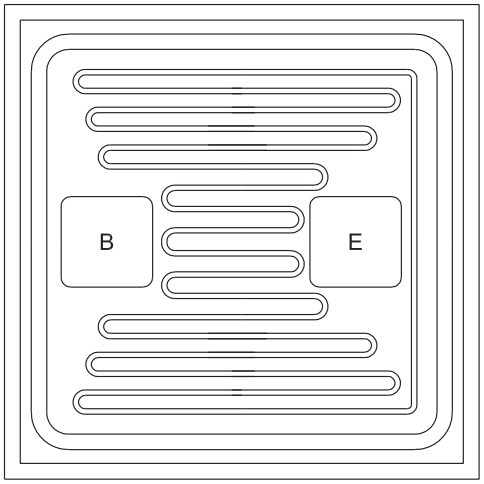
Small Signal Transistor

NPN - Low $V_{CE(SAT)}$ Transistor Chip

PROCESS DETAILS

Die Size	26 x 26 MILS
Die Thickness	5.9 MILS
Base Bonding Pad Area	5.5 x 5.5 MILS
Emitter Bonding Pad Area	5.5 x 5.5 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 5 INCH WAFER

25,536

PRINCIPAL DEVICE TYPES

CMLT3820G
CMPT3820
CXT3820

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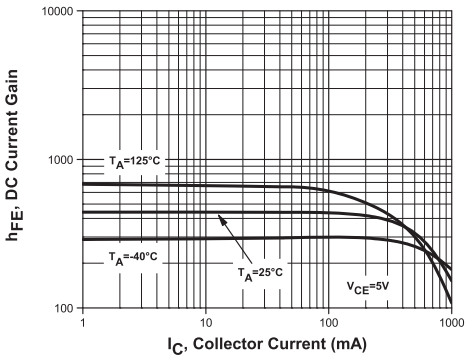
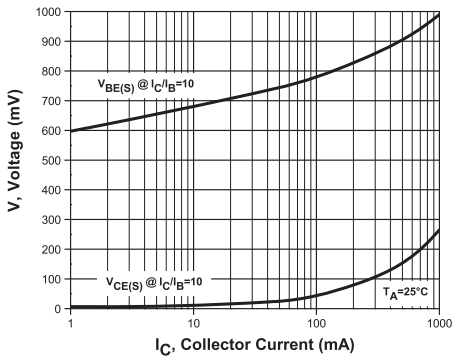
PROCESS CP382X

Typical Electrical Characteristics

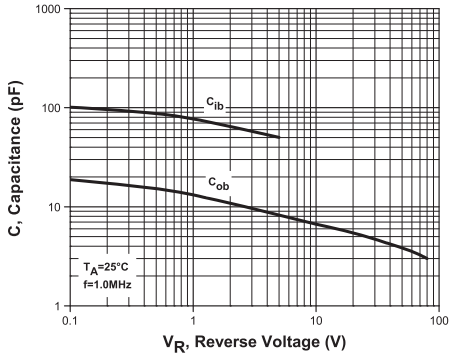
DC Current Gain



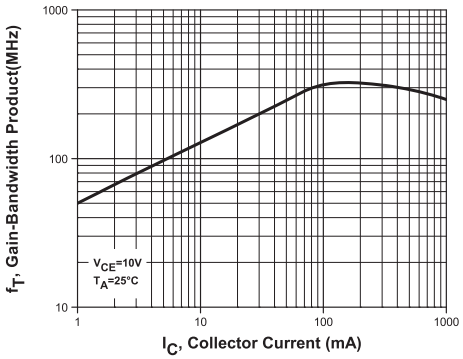
"ON" Voltage



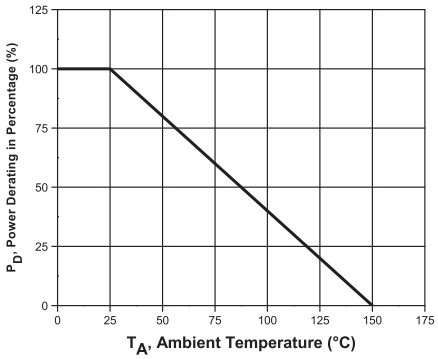
Capacitance



Current Gain-Bandwidth Product



Normalized Power Derating



R0 (9-September 2010)